## MC100LVELT22

## Translator, Dual LVTTL / LVCMOS to Differential LVPECL

## Description

The MC100LVELT22 is a dual LVTTL/LVCMOS to differential LVPECL translator. Due to LVPECL (Low Voltage Positive ECL) levels, only +3.3 V and ground is required. The small 8 -lead package outline with low skew dual gate design makes the MC100LVELT22 ideal for applications which require translation of a clock and/or data signal.

Features

- 350 ps Typical Propagation Delay
- <100 ps Output-to-Output Skew
- Flow Through Pinouts
- The 100 Series Contains Temperature Compensation
- LVPECL Operating Range: $\mathrm{V}_{\mathrm{CC}}=3.15 \mathrm{~V}$ to 3.45 V with GND $=0 \mathrm{~V}$
- When Unused TTL Input is left Open, Q Output will Default High
- These are $\mathrm{Pb}-$ Free Devices

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A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
M = Date Code

- = Pb-Free Package
(Note: Microdot may be in either location)
*For additional marking information, refer to Application Note AND8002/D.


## ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

## MC100LVELT22



Table 1. PIN DESCRIPTION

| PIN | FUNCTION |
| :--- | :--- |
| Qn, $\overline{\text { Qn }}$ | LVPECL Differential Outputs |
| D0, D1 | LVTTL/LVCMOS Inputs |
| VCC $_{\text {CC }}$ | Positive Supply |
| GND | Ground |

Figure 1. 8-Lead Pinout (Top View) and Logic Diagram

Table 2. ATTRIBUTES

| Characteristics | Value |
| :---: | :---: |
| Internal Input Pulldown Resistor | N/A |
| Internal Input Pullup Resistor | N/A |
| ESD Protection $\begin{gathered}\text { Human Body Model } \\ \text { Machine Model }\end{gathered}$ | $\begin{aligned} & >4 \mathrm{kV} \\ & >200 \mathrm{~V} \end{aligned}$ |
| Moisture Sensitivity, Indefinite Time Out of Drypack (Note 1) SOIC-8 TSSOP-8 | Level 1 <br> Level 3 |
| Flammability Rating Oxygen Index: 28 to 34 | UL 94 V-0 @ 0.125 in |
| Transistor Count | 164 |
| Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test |  |

1. For additional information, see Application Note AND8003/D.

Table 3. MAXIMUM RATINGS

| Symbol | Parameter | Condition 1 | Condition 2 | Rating | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\text {CC }}$ | Positive Power Supply | GND $=0 \mathrm{~V}$ |  | 7 | V |
| $\mathrm{V}_{1}$ | Input Voltage | GND $=0 \mathrm{~V}$ | $\mathrm{V}_{\mathrm{I}} \leq \mathrm{V}_{\mathrm{CC}}$ | 7 | V |
| ${ }_{\text {out }}$ | Output Current | Continuous Surge |  | $\begin{gathered} 50 \\ 100 \end{gathered}$ | $\begin{aligned} & \mathrm{mA} \\ & \mathrm{~mA} \end{aligned}$ |
| TA | Operating Temperature Range |  |  | -40 to +85 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\text {stg }}$ | Storage Temperature Range |  |  | -65 to +150 | ${ }^{\circ} \mathrm{C}$ |
| $\theta_{\mathrm{JA}}$ | Thermal Resistance (Junction-to-Ambient) | 0 Ifpm 500 lfpm | $\begin{aligned} & \hline \text { SO-8 } \\ & \text { SO-8 } \end{aligned}$ | $\begin{aligned} & 190 \\ & 130 \end{aligned}$ | $\begin{aligned} & \hline{ }^{\circ} \mathrm{C} / \mathrm{W} \\ & { }^{\circ} \mathrm{C} / \mathrm{w} \end{aligned}$ |
| $\theta_{\text {Jc }}$ | Thermal Resistance (Junction-to-Case) | std bd | SO-8 | 41 to $44 \pm 5 \%$ | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| $\theta_{\mathrm{JA}}$ | Thermal Resistance (Junction-to-Ambient) | $\begin{aligned} & \hline 0 \text { lfpm } \\ & 500 \text { lfpm } \end{aligned}$ | $\begin{aligned} & \hline \text { TSSOP-8 } \\ & \text { TSSOP-8 } \end{aligned}$ | $\begin{aligned} & \hline 185 \\ & 140 \end{aligned}$ | $\begin{aligned} & \hline{ }^{\circ} \mathrm{C} / \mathrm{W} \\ & { }^{\circ} \mathrm{C} / \mathrm{w} \end{aligned}$ |
| $\theta_{\text {Jc }}$ | Thermal Resistance (Junction-to-Case) | std bd | TSSOP-8 | 41 to $44 \pm 5 \%$ | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| $\mathrm{T}_{\text {sol }}$ | Wave Solder Pb-Free | <2 to $3 \mathrm{sec} @ 260^{\circ} \mathrm{C}$ |  | 265 | ${ }^{\circ} \mathrm{C}$ |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
2. JEDEC standard multilayer board - 2S2P (2 signal, 2 power)

Table 4. LVPECL DC CHARACTERISTICS $\mathrm{V}_{\mathrm{CC}}=3.3 \mathrm{~V} ; \mathrm{GND}=0.0 \mathrm{~V}$ (Note 3)

| Symbol | Characteristic | $-40^{\circ} \mathrm{C}$ |  |  | $25^{\circ} \mathrm{C}$ |  |  | $85^{\circ} \mathrm{C}$ |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  | Min | Typ | Max | Min | Typ | Max | Min | Typ | Max |  |
| ICC | Power Supply Current |  |  | 28 |  |  | 28 |  |  | 29 | mA |
| $\mathrm{V}_{\mathrm{OH}}$ | Output HIGH Voltage (Note 4) | 2275 |  | 2420 | 2275 |  | 2420 | 2275 |  | 2420 | mV |
| $\mathrm{V}_{\text {OL }}$ | Output LOW Voltage (Note 4) | 1490 |  | 1680 | 1490 |  | 1680 | 1490 |  | 1680 | mV |

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.
3. Output parameters vary $1: 1$ with $\mathrm{V}_{\mathrm{CC}}$. $\mathrm{V}_{\mathrm{CC}}$ can vary $\pm 0.15 \mathrm{~V}$.
4. Outputs are terminated through a 50 ohm resistor to $\mathrm{V}_{\mathrm{CC}}-2 \mathrm{~V}$.

Table 5. LVTTL/LVCMOS INPUT DC CHARACTERISTICS $\mathrm{V}_{\mathrm{CC}}=3.3 \mathrm{~V} ; \mathrm{T}_{\mathrm{A}}=-40^{\circ} \mathrm{C}$ to $85^{\circ} \mathrm{C}$ (Note 5)

| Symbol | Characteristic | Min | Typ | Max | Unit | Condition |
| :--- | :--- | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{I}_{\mathrm{IH}}$ | Input HIGH Current |  |  | 20 | $\mu \mathrm{~A}$ | $\mathrm{~V}_{\mathrm{IN}}=2.7 \mathrm{~V}$ |
| $\mathrm{I}_{\mathrm{IHH}}$ | Input HIGH Current |  |  | 100 | $\mu \mathrm{~A}$ | $\mathrm{~V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{CC}}$ |
| $\mathrm{I}_{\mathrm{IL}}$ | Input LOW Current |  |  | -0.2 | mA | $\mathrm{~V}_{\mathrm{IN}}=0.5 \mathrm{~V}$ |
| $\mathrm{~V}_{\mathrm{IK}}$ | Input Clamp Diode Voltage |  |  | -1.2 | V | $\mathrm{I}_{\mathrm{IN}}=-18 \mathrm{~mA}$ |
| $\mathrm{~V}_{\mathrm{IH}}$ | Input HIGH Voltage | 2.0 |  | 3.3 | V |  |
| $\mathrm{~V}_{\mathrm{IL}}$ | Input LOW Voltage | 0 |  | 0.8 | V |  |

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 Ifpm.
5. $\mathrm{V}_{\mathrm{CC}}$ can vary $\pm 0.15 \mathrm{~V}$.

Table 6. AC CHARACTERISTICS $\mathrm{V}_{\mathrm{CC}}=3.3 \mathrm{~V}$; $\mathrm{GND}=0.0 \mathrm{~V}$ (Note 6)

| Symbol | Characteristic | -40 ${ }^{\circ} \mathrm{C}$ |  |  | $25^{\circ} \mathrm{C}$ |  |  | $85^{\circ} \mathrm{C}$ |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  | Min | Typ | Max | Min | Typ | Max | Min | Typ | Max |  |
| $\mathrm{f}_{\text {max }}$ | Maximum Toggle Frequency |  |  |  |  | 350 |  |  |  |  | MHz |
| ${ }^{\text {t PLH }}$ | Propagation Delay (Note 7) | 200 | 350 | 600 | 200 | 350 | 600 | 200 | 350 | 600 | ps |
| ${ }^{\text {skew }}$ | Skew $\begin{array}{r}\text { Output-to-Output } \\ \text { Part-to-Part }\end{array}$ |  | 30 | $\begin{aligned} & 100 \\ & 400 \end{aligned}$ |  | 30 | $\begin{aligned} & 100 \\ & 400 \end{aligned}$ |  | 30 | $\begin{aligned} & 100 \\ & 400 \end{aligned}$ | ps |
| ${ }^{\text {t }}$ ITTEER | Random Clock Jitter (RMS) |  |  | 2.1 |  | 1.1 | 1.9 |  |  | 1.6 | ps |
| $\mathrm{tjit}^{\text {( }}$ ) | Additive RMS Phase Jitter $\mathrm{f}_{\mathrm{C}}=50 \mathrm{MHz}$, Integration Range: 12 kHz to 20 MHz (See Figure 2) |  |  |  |  | 219 |  |  |  |  | fs |
| ${ }_{\text {t }}^{\text {r }}$ /ff | Output Rise/Fall Time (20-80\%) | 200 |  | 550 | 200 |  | 500 | 200 |  | 500 | ps |

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 Ifpm.
6. $\mathrm{V}_{\mathrm{CC}}$ can vary $\pm 0.15 \mathrm{~V}$. Outputs are terminated through a $50 \Omega$ resistor to $\mathrm{V}_{\mathrm{CC}}-2 \mathrm{~V}$.
7. Specifications for standard TTL input signal.

## MC100LVELT22



Figure 2. Typical MC100LVELT22 Phase Noise Plot at $\mathrm{f}_{\text {Carrier }}=50 \mathrm{MHz}, \mathrm{V}_{\mathrm{CC}}=3.3 \mathrm{~V}, \mathbf{2 5}^{\circ} \mathrm{C}$

The above phase noise data was captured using Agilent E5052A/B. The data displays the input phase noise and output phase noise used to calculate the additive phase jitter at a specified integration range. The additive RMS phase jitter contributed by the device (integrated between 12 kHz and 20 MHz ) is 219 fs . The additive RMS phase jitter performance of the translator is highly dependent on the phase noise of the input source.

To obtain the most precise additive phase noise measurement, it is vital that the source phase noise be
notably lower than that of the DUT. If the phase noise of the source is greater than the noise floor of the device under test, the source noise will dominate the additive phase jitter calculation and lead to an incorrect negative result for the additive phase noise within the integration range. The Figure above is a good example of the MC100LVELT22 source generator phase noise having a significantly lower floor than the DUT and results in an additive phase jitter of 219 fs .

$$
\text { Additive RMS phase jitter }=\sqrt{\text { RMS phase jitter of output }^{2}-\text { RMS phase jitter of input }^{2}}
$$

$$
219 \mathrm{fs}=\sqrt{587.92 \mathrm{fs}^{2}-545.23 \mathrm{fs}^{2}}
$$

Figure 2 was created with measured data from Agilent-E5052B Signal Source Analyzer using ON Semiconductor Phase Noise Explorer web tool. This free application enables an interactive environment for advanced
phase noise and jitter analysis of timing devices and clock tree designs. To see the performance of MC100LVELT22 beyond conditions outlined in this datasheet, please visit the ON Semiconductor Green Point Design Tools homepage.

## MC100LVELT22



Figure 3. Typical Termination for Output Driver and Device Evaluation (See Application Note AND8020/D - Termination of ECL Logic Devices.)

ORDERING INFORMATION

| Device | Package | Shipping $^{\dagger}$ |
| :--- | :--- | :---: |
| MC100LVELT22DG | SOIC-8 <br> (Pb-Free) | 98 Units / Rail |
| MC100LVELT22DR2G | SOIC-8 <br> (Pb-Free) | $2500 /$ Tape \& Reel |
| MC100LVELT22DTG | TSSOP-8 |  |
| (Pb-Free) | 100 Units / Rail |  |
| MC100LVELT22DTRG | TSSOP-8 |  |

$\dagger$ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
Resource Reference of Application Notes
AN1405/D - ECL Clock Distribution Techniques
AN1406/D - Designing with PECL (ECL at +5.0 V)
AN1503/D - ECLinPS ${ }^{\text {m }}$ I/O SPiCE Modeling Kit
AN1504/D - Metastability and the ECLinPS Family
AN1568/D - Interfacing Between LVDS and ECL
AN1672/D - The ECL Translator Guide
AND8001/D - Odd Number Counters Design
AND8002/D - Marking and Date Codes
AND8020/D - Termination of ECL Logic Devices
AND8066/D - Interfacing with ECLinPS
AND8090/D - AC Characteristics of ECL Devices


SOIC-8 NB
CASE 751-07
ISSUE AK
SCALE 1:1
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
. CONTROLLING DIMENSION: MILLIMETER.
2. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
3. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
4. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
5. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

| DIM | MILLIMETERS |  | INCHES |  |
| :---: | :---: | :---: | :---: | :---: |
|  | MIN | MAX | MIN | MAX |
|  | 4.80 | 5.00 | 0.189 | 0.197 |
| B | 3.80 | 4.00 | 0.150 | 0.157 |
| C | 1.35 | 1.75 | 0.053 | 0.069 |
| D | 0.33 | 0.51 | 0.013 | 0.020 |
| G | 1.27 BSC |  | 0.050 BSC |  |
| H | 0.10 | 0.25 | 0.004 | 0.010 |
| J | 0.19 | 0.25 | 0.007 | 0.010 |
| K | 0.40 | 1.27 | 0.016 | 0.050 |
| M | 0 | $0^{\circ}$ | $8^{\circ}$ | 0 |
|  | $\circ$ | 8 |  |  |
| N | 0.25 | 0.50 | 0.010 | 0.020 |
| S | 5.80 | 6.20 | 0.228 | 0.244 |

GENERIC
MARKING DIAGRAM*



XXXXX = Specific Device Code
A = Assembly Location
L Wafer Lot
= Year
= Work Week
= Pb-Free Package
*This information is generic. Please refer to device data sheet for actual part marking. $\mathrm{Pb}-\mathrm{Free}$ indicator, " G " or microdot " $\mathrm{=}$ ", may or may not be present. Some products may not follow the Generic Marking.
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## STYLES ON PAGE 2

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SOIC-8 NB
CASE 751-07
ISSUE AK
DATE 16 FEB 2011

STYLE

| PIN 1. | EMITTER |
| ---: | :--- |
| 2. | COLLECTOR |
| 3. | COLLECTOR |
| 4. | EMITTER |
| 5. | EMITTER |
| 6. | BASE |
| 7. | BASE |
| 8. | EMITTER |
| STYLE 5: |  |
| PIN 1. | DRAIN |
| 2. | DRAIN |
| 3. | DRAIN |
| 4. | DRAIN |
| 5. | GATE |
| 6. | GATE |
| 7. | SOURCE |
| 8. | SOURCE |

STYLE 9:
PIN 1. EMITTER, COMMON
COLLECTOR, DIE \#1 COLLECTOR, DIE \#2 EMITTER, COMMON EMITTER, COMMON BASE, DIE \#2
BASE, DIE \#1
8. EMITTER, COMMON

STYLE 13:
PIN 1. N.C.
2. SOURCE
3. SOURCE

GATE
DRAIN
DRAIN
DRAIN
8. DRAIN

STYLE 17:
PIN 1. VCC
V2OUT
V10UT
V10UT
TXE
RXE
VEE
8. ACC

STYLE 21:
PIN 1. CATHODE 1
2. CATHODE 2
3. CATHODE 3

CATHODE 4
CATHODE 5
6. COMMON ANODE
7. COMMON ANODE
8. CATHODE 6

STYLE 25:
PIN 1. VIN
2. $N / C$

REXT
GND
IOUT
IOUT
IOUT
8. IOUT

## STYLE 29:

PIN 1. BASE, DIE \#
EMITTER, \#1
BASE, \#2
. EMITTER, \#2
5. COLLECTOR, \#2
6. COLLECTOR, \#2
7. COLLECTOR, \#1
7. COLLECTOR, \#1

STYLE
PIN 1. COLIECTOR, DIE,
2. COLLECTOR, \#1
3. COLLECTOR, \#2

COLLECTOR, \#2
BASE, \#2
. EMITTER, \#2
7. BASE, \#1
8. EMITTER, \#1

STYLE 6:
PIN 1. SOURCE
DRAIN
3. DRAIN
4. SOURCE

SOURCE
6. GATE
7. GATE
8. SOURCE

STYLE 10:
PIN 1. GROUND
2. BIAS 1
3. OUTPUT

GROUND
GROUND
BIAS 2
7. INPUT
8. GROUND

STYLE 14:
PIN 1. N-SOURCE
2. N-GATE

P-SOURCE
P-GATE
5-DRAIN
. P-DRAIN
7. N -DRAIN
8. N-DRAIN

STYLE 18
PIN 1. ANODE
2. ANODE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. CATHODE
8. CATHODE

STYLE 22 :
PIN 1. I/O LINE
2. COMMON CATHODE/VCC
3. COMMON CATHODE/VCC
4. I/O LINE 3
5. COMMON ANODE/GND
6. I/O LINE 4
7. I/O LINE 5
8. COMMON ANODE/GND

STYLE 26:
PIN 1. GND
2. $\mathrm{dv} / \mathrm{dt}$
3. ENABLE
4. ILIMIT
5. SOURCE

SOURCE
7. SOURCE
8. VCC

STYLE 30:
PIN 1. DRAIN 1
2. DRAIN 1
. GATE 2
4. SOURCE 2
5. SOURCE 1/DRAIN 2
. SOURCE 1/DRAIN 2
SOURCE 1/DRAIN 2
8. GATE 1

STYLE 3
STYLE
N 1. DRAIN, DIE
2. DRAIN, \#1
3. DRAIN, \#2
4. DRAIN, \#2
5. GATE, \#2
7. GATE, \#1
8. SOURCE, \#1

## STYLE 7

PIN 1. INPUT
2. EXTERNAL BYPASS
3. THIRD STAGE SOURCE
4. GROUND
5. DRAIN
6. GATE 3
7. SECOND STAGE Vd
8. FIRST STAGE Vd

## STYLE 11:

PIN 1. SOURCE
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. DRAIN 2
7. DRAIN 1
8. DRAIN 1

## STYLE 15:

PIN 1. ANODE 1
2. ANODE 1
3. ANODE 1
4. ANODE 1
5. CATHODE, COMMON
6. CATHODE, COMMON
7. CATHODE, COMMON
8. CATHODE, COMMON

## STYLE 19:

PIN 1. SOURCE
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. MIRROR 2
7. DRAIN 1
8. MIRROR 1

## STYLE 23:

PIN 1. LINE 1 IN
2. COMMON ANODE/GND
3. COMMON ANODE/GND
4. LINE 2 IN
5. LINE 2 OUT
6. COMMON ANODE/GND
7. COMMON ANODE/GND
8. LINE 1 OUT

STYLE 27:
PIN 1. ILIMIT
2. OVLO
3. UVLO
4. INPUT+
5. INPUT+
5. SOURCE
6. SOURCE
7. SOURCE
8. DRAIN

STYLE 4:
PIN 1. ANODE
2. ANODE
3. ANODE
4. ANODE
5. ANODE
6. ANODE
8. COMMON CATHODE

## STYLE 8:

PIN 1. COLLECTOR, DIE \#1
2. BASE, \#1
3. BASE, \#2
4. COLLECTOR, \#2
5. COLLECTOR, \#2
6. EMITTER, \#2
7. EMITTER, \#1
8. COLLECTOR, \#1

## STYLE 12

PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

## STYLE 16:

PIN 1. EMITTER, DIE \#1
2. BASE, DIE \#1
3. EMITTER, DIE \#2
3. EMITTER, DIE
4. BASE, DIE \#2
4. BASE, DIE \#2
6. COLLECTOR, DIE \#2
7. COLLECTOR, DIE \#1
8. COLLECTOR, DIE \#1

## STYLE 20:

PIN 1. SOURCE (N)
2. GATE (N)
3. SOURCE (P)
4. GATE (P)
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

## STYLE 24:

PIN 1. BASE
2. EMITTER
3. COLLECTOR/ANODE
4. COLLECTOR/ANODE
5. CATHODE
6. CATHODE
7. COLLECTOR/ANODE
8. COLLECTOR/ANODE

## STYLE 28:

PIN 1. SW_TO_GND
2. DASIC $\bar{O} F F$
3. DASIC_SW_DET
4. GND
5. V_MON
6. VBUULK
7. VBULK
8. VIN

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TSSOP 8

## CASE 948R-02

ISSUE A
DATE 04/07/2000

## SCALE 2:1


notes:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PROTRUSI
PER SIDE
5. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY
6. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-

|  | MILLIMETERS |  | INCHES |  |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| DIM | MIN | MAX | MIN | MAX |  |  |
| A | 2.90 | 3.10 | 0.114 | 0.122 |  |  |
| B | 2.90 | 3.10 | 0.114 | 0.122 |  |  |
| C | 0.80 | 1.10 | 0.031 | 0.043 |  |  |
| D | 0.05 | 0.15 | 0.002 | 0.006 |  |  |
| F | 0.40 | 0.70 | 0.016 | 0.028 |  |  |
| G | 0.65 BSC |  | 0.026 BSC |  |  |  |
| K | 0.25 |  | 0.40 | 0.010 |  | 0.016 |
| L | 4.90 BSC |  | 0.193 BSC |  |  |  |
| M | $0^{\circ}$ |  | $6^{\circ}$ | $0^{\circ}$ |  | $6^{\circ}$ |


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